

## **isc** Silicon NPN Power Transistor

# 2SC4293

#### DESCRIPTION

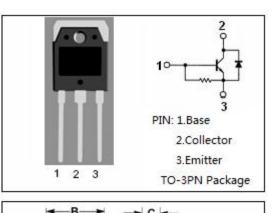
- · High Breakdown Voltage-
- : V<sub>(BR)CBO</sub>= 1500V(Min)
- High Switching Speed
- Built-in Damper Diode
- Good Linearity of h<sub>FE</sub>

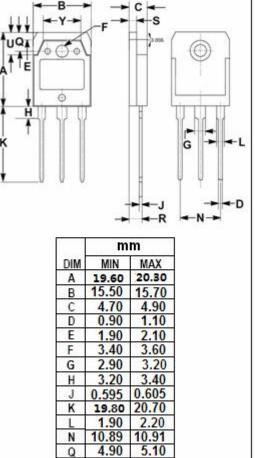
 Minimum Lot-to-Lot variations for robust device performance and reliable operation

### **APPLICATIONS**

· Ultrahigh-definition color display horizontal deflection output applications

SYMBOL	PARAMETER	VALUE	UNIT	
Vсво	Collector-Base Voltage	tage 1500		
V <sub>CEO</sub>	Collector-Emitter Voltage	800	V	
V <sub>EBO</sub>	Emitter-Base Voltage	7	V	
lc	Collector Current-Continuous		А	
I <sub>CP</sub>	Collector Current-Peak	16	A	
Pc	Collector Power Dissipation @ $T_a=25^{\circ}C$	3.0	W	
	Collector Power Dissipation @ $T_C=25^{\circ}C$	50		
TJ	Junction Temperature 150		Ĉ	
T <sub>stg</sub>	Storage Temperature Range	-55~150	°C	





R

S

U

Y

3.35

1.995

5.90

3.45

2.100

6.20 9.90 10.10



### **INCHANGE SEMICONDUCTOR**

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### ELECTRICAL CHARACTERISTICS

#### $T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 0.1A; I <sub>B</sub> = 0	800			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 4A; I <sub>B</sub> = 1A			5.0	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 4A; I <sub>B</sub> = 1A			1.5	V
І <sub>сво</sub>	Collector Cutoff Current	V <sub>CB</sub> = 800V; I <sub>E</sub> = 0			10	μA
Ices	Collector Cutoff Current	V <sub>CE</sub> = 1500V; R <sub>BE</sub> = 0			1.0	mA
I <sub>EBO</sub>	Emitter Cutoff Current	$V_{EB}=4V; I_{C}=0$	40		130	mA
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> = 1A; V <sub>CE</sub> = 5V	8			
h <sub>FE-2</sub>	DC current gain	Ic= 4A; Vce= 5V	4		6	
V <sub>ECF</sub>	C-E Diode Forward Voltage	I <sub>F</sub> = 5A			2.0	V

Switching times

t <sub>stg</sub>	Storage Time	Ic= 4A, I <sub>B1</sub> = 0.8A; I <sub>B2</sub> = -1.6A; V <sub>CC</sub> = 200V		3.0	μ \$
tf	Fall Time			0.3	μ <b>S</b>
NOTICE					

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